

# Enhancement Mode N-Channel Power MOSFET

## Features

- ◆ Low  $R_{DS(on)}$  & FOM
- ◆ Extremely low switching loss
- ◆ Excellent stability and uniformity
- ◆ Easy to drive

## Applications

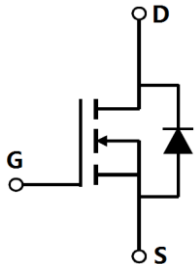
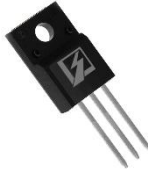
- ◆ Lighting
- ◆ Hard switching PWM
- ◆ Server power supply
- ◆ Charger

## ■ General Description

OSG65R260FSF\_NB uses advanced GreenMOS™ technology to provide low  $R_{DS(ON)}$ , low gate charge, fast switching and excellent avalanche characteristics. This device is suitable for active power factor correction and switching mode power supply applications.

◆ $V_{DS, min@T_{jmax}}$	700 V
◆ $I_{D, pulse}$	45 A
◆ $R_{DS(ON), max @ V_{GS}=10 V}$	260 mΩ
◆ $Q_g$	26.4 nC

## ■ Schematic and Package Information

<b>Schematic Diagram</b> 	<b>Pin Assignment Top View</b>  <b>TO220F</b> <b>OSG65R260FSF_NB</b>
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## ■ Absolute Maximum Ratings at $T_j=25^{\circ}\text{C}$ unless otherwise noted

Parameter	Symbol	Value	Unit
Drain source voltage	$V_{DS}$	650	V
Gate source voltage	$V_{GS}$	±30	V
Continuous drain current <sup>1)</sup> , $T_C=25^{\circ}\text{C}$	$I_D$	15	A
Continuous drain current <sup>1)</sup> , $T_C=100^{\circ}\text{C}$		9.5	
Pulsed drain current <sup>2)</sup> , $T_C=25^{\circ}\text{C}$	$I_{D, pulse}$	45	A
Continuous diode forward current <sup>1)</sup> , $T_C=25^{\circ}\text{C}$	$I_S$	15	A
Diode pulsed current <sup>2)</sup> , $T_C=25^{\circ}\text{C}$	$I_{S, pulse}$	45	A
Power dissipation <sup>3)</sup> , $T_C=25^{\circ}\text{C}$	$P_D$	33	W
Single pulsed avalanche energy <sup>5)</sup>	$E_{AS}$	360	mJ
MOSFET dv/dt ruggedness, $V_{DS}=0\text{...}480\text{ V}$	dv/dt	50	V/ns
Reverse diode dv/dt, $V_{DS}=0\text{...}480\text{ V}$ , $I_{SD}\leq I_D$	dv/dt	15	V/ns
Operation and storage temperature	$T_{stg}, T_j$	-55 to 150	°C

## ■ Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal resistance, junction-case	$R_{\theta JC}$	3.8	$^{\circ}\text{C}/\text{W}$
Thermal resistance, junction-ambient <sup>4)</sup>	$R_{\theta JA}$	62.5	$^{\circ}\text{C}/\text{W}$

## ■ Electrical Characteristics at $T_j=25^{\circ}\text{C}$ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Drain-source breakdown voltage	$BV_{DSS}$	650			V	$V_{GS}=0\text{ V}, I_D=250\ \mu\text{A}$
		700				$V_{GS}=0\text{ V}, I_D=250\ \mu\text{A}, T_j=150^{\circ}\text{C}$
Gate threshold voltage	$V_{GS(th)}$	2.9		3.9	V	$V_{DS}=V_{GS}, I_D=250\ \mu\text{A}$
Drain-source on-state resistance	$R_{DS(on)}$		0.22	0.26	$\Omega$	$V_{GS}=10\text{ V}, I_D=7.5\text{ A}$
			0.54			$V_{GS}=10\text{ V}, I_D=7.5\text{ A}, T_j=150^{\circ}\text{C}$
Gate-source leakage current	$I_{GSS}$			100	nA	$V_{GS}=30\text{ V}$
				-100		$V_{GS}=-30\text{ V}$
Drain-source leakage current	$I_{DSS}$			1	$\mu\text{A}$	$V_{DS}=650\text{ V}, V_{GS}=0\text{ V}$
Gate resistance	$R_G$		8.3		$\Omega$	$f=1\text{ MHz}, \text{ Open drain}$

## ■ Dynamic Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Input capacitance	$C_{iss}$		1227		pF	$V_{GS}=0\text{ V}, V_{DS}=50\text{ V}, f=100\text{ kHz}$
Output capacitance	$C_{oss}$		100.2		pF	
Reverse transfer capacitance	$C_{rss}$		7.1		pF	
Turn-on delay time	$t_{d(on)}$		24.7		ns	$V_{GS}=10\text{ V}, V_{DS}=400\text{ V}, R_G=2\ \Omega, I_D=8\text{ A}$
Rise time	$t_r$		7.3		ns	
Turn-off delay time	$t_{d(off)}$		56.3		ns	
Fall time	$t_f$		9.5		ns	

## ■ Gate Charge Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Total gate charge	$Q_g$		26.4		nC	$I_D=8\text{ A}$ , $V_{DS}=400\text{ V}$ , $V_{GS}=10\text{ V}$
Gate-source charge	$Q_{gs}$		7.8		nC	
Gate-drain charge	$Q_{gd}$		7.9		nC	
Gate plateau voltage	$V_{\text{plateau}}$		5.3		V	

## ■ Body Diode Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Diode forward voltage	$V_{SD}$			1.4	V	$I_S=15\text{ A}$ , $V_{GS}=0\text{ V}$
Reverse recovery time	$t_{rr}$		292		ns	$V_R=400\text{ V}$ , $I_S=8\text{ A}$ , $di/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge	$Q_{rr}$		3.5		$\mu\text{C}$	
Peak reverse recovery current	$I_{rrm}$		21.8		A	

## ■ Note

- 1) Calculated continuous current based on maximum allowable junction temperature.
- 2) Repetitive rating; pulse width limited by max. junction temperature.
- 3)  $P_d$  is based on max. junction temperature, using junction-case thermal resistance.
- 4) The value of  $R_{\theta JA}$  is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with  $T_a=25\text{ }^\circ\text{C}$ .
- 5)  $V_{DD}=100\text{ V}$ ,  $R_G=50\text{ }\Omega$ ,  $L=79.9\text{ mH}$ , starting  $T_j=25\text{ }^\circ\text{C}$ .

■ **Electrical Characteristics Diagrams**

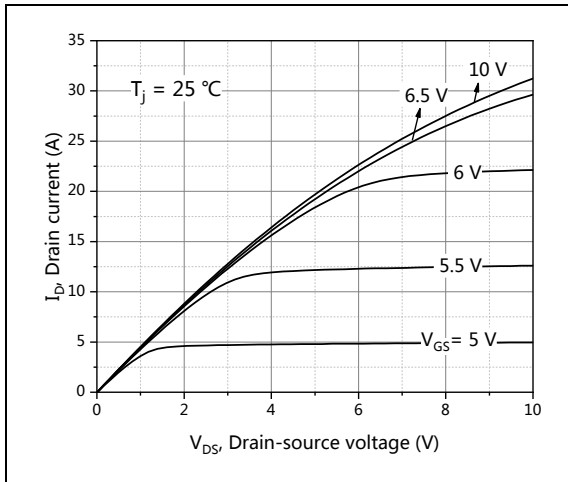


Figure 1, Typ. output characteristics

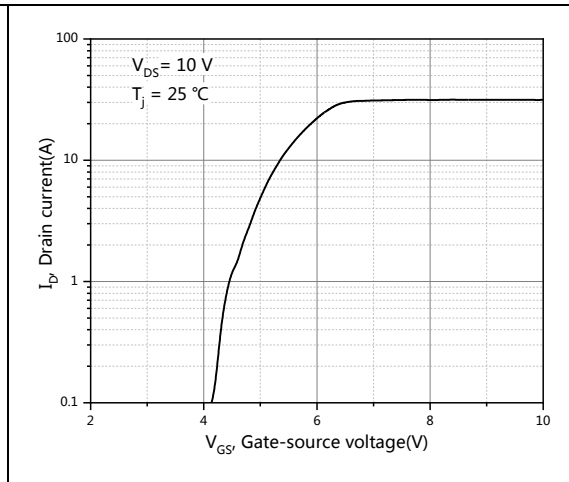


Figure 2, Typ. transfer characteristics

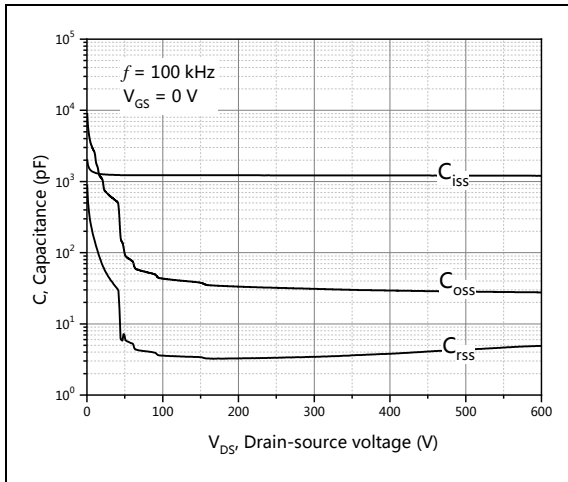


Figure 3, Typ. capacitances

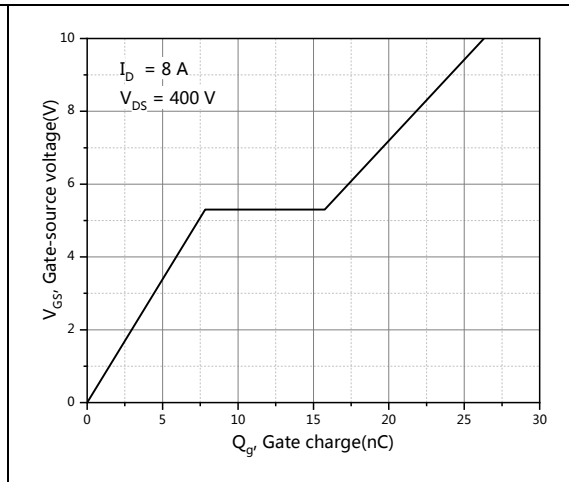


Figure 4, Typ. gate charge

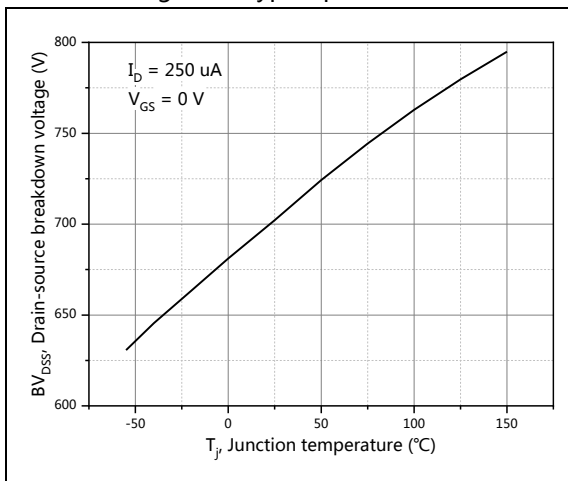


Figure 5, Drain-source breakdown voltage

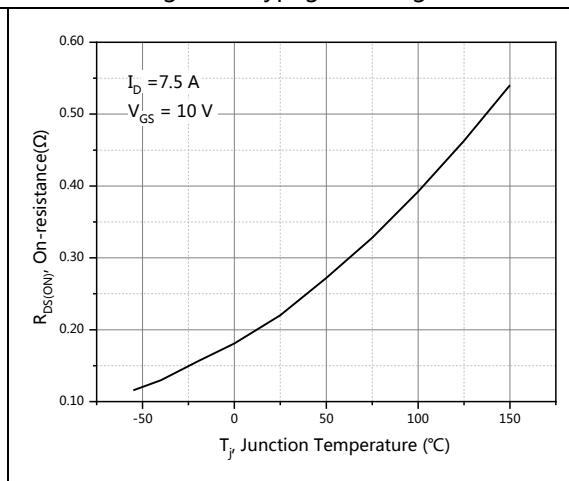


Figure 6, Drain-source on-state resistance

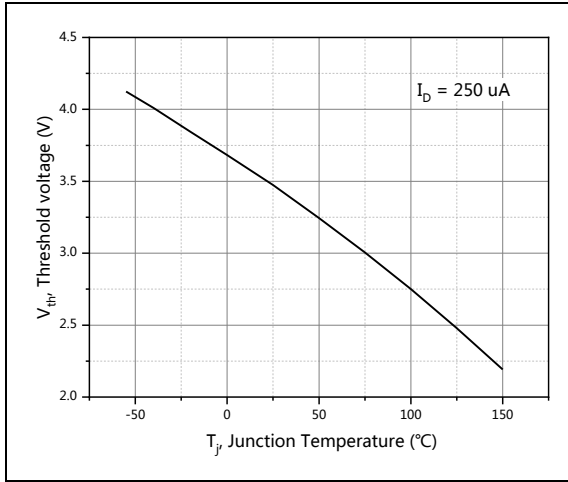


Figure 7, Threshold voltage

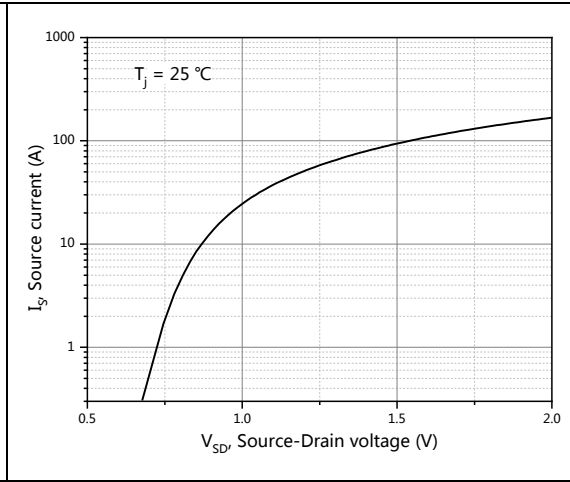


Figure 8, Forward characteristic of body diode

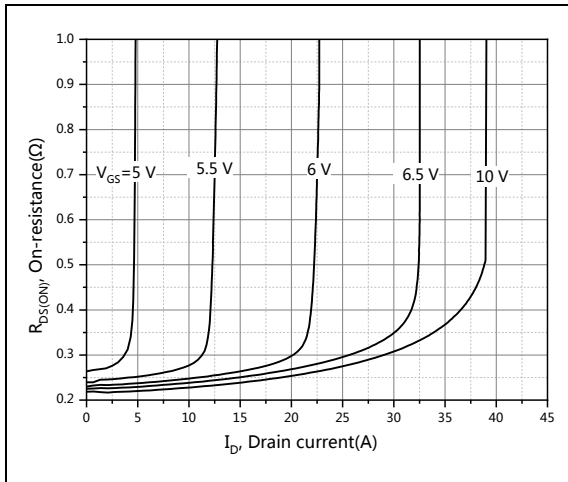


Figure 9, Drain-source on-state resistance

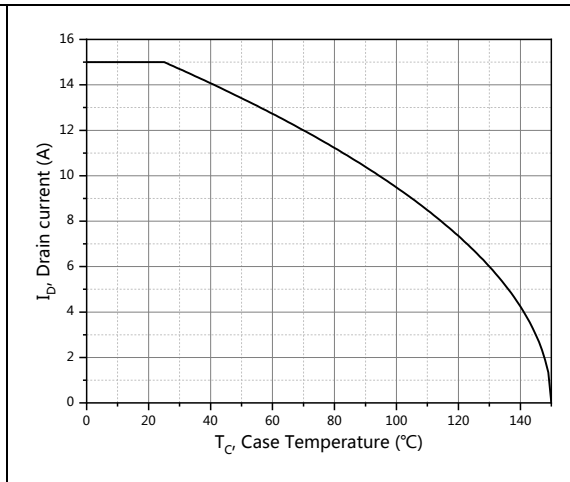


Figure 10, Drain current

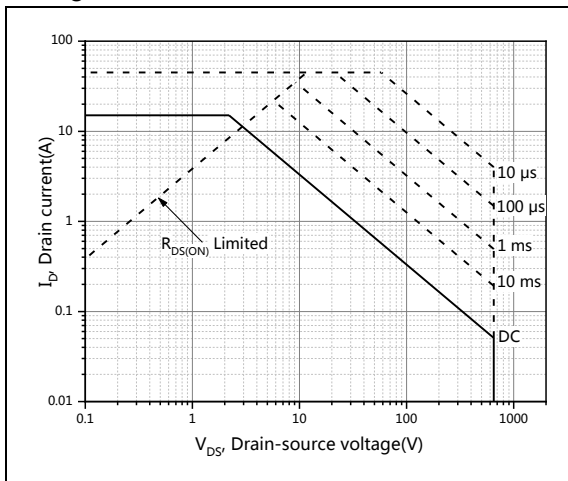


Figure 11, Safe operation area  $T_c=25\text{ }^\circ\text{C}$

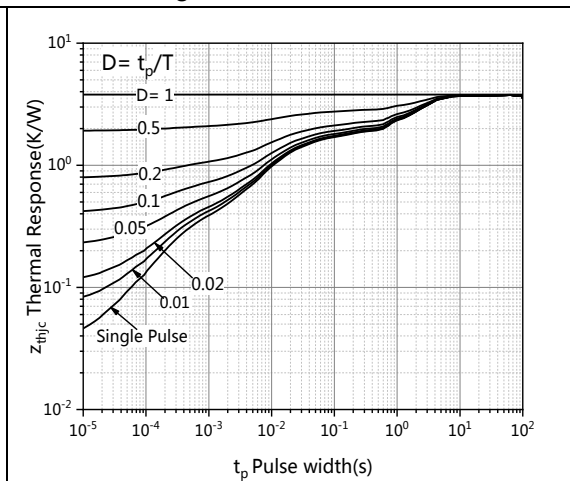


Figure 12, Max. transient thermal impedance

■ Test circuits and waveforms

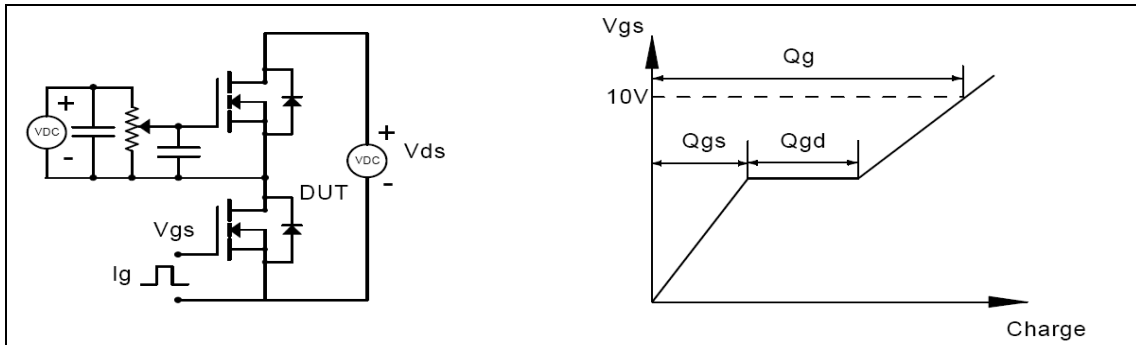


Figure 1, Gate charge test circuit & waveform

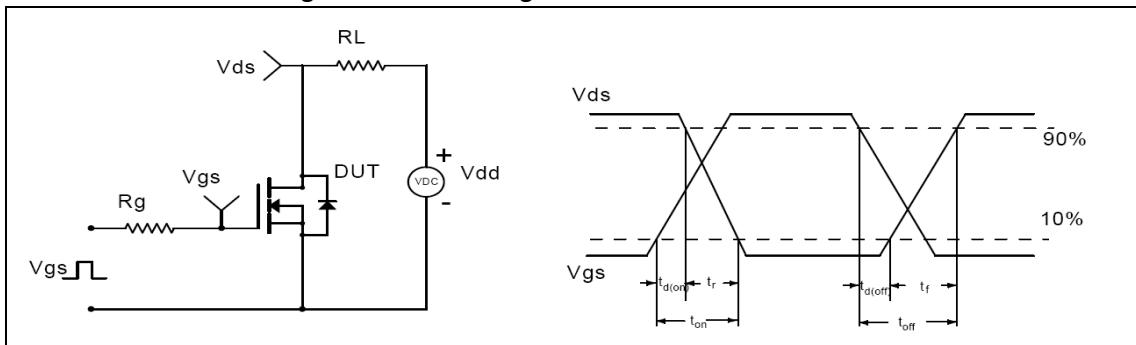


Figure 2, Switching time test circuit & waveforms

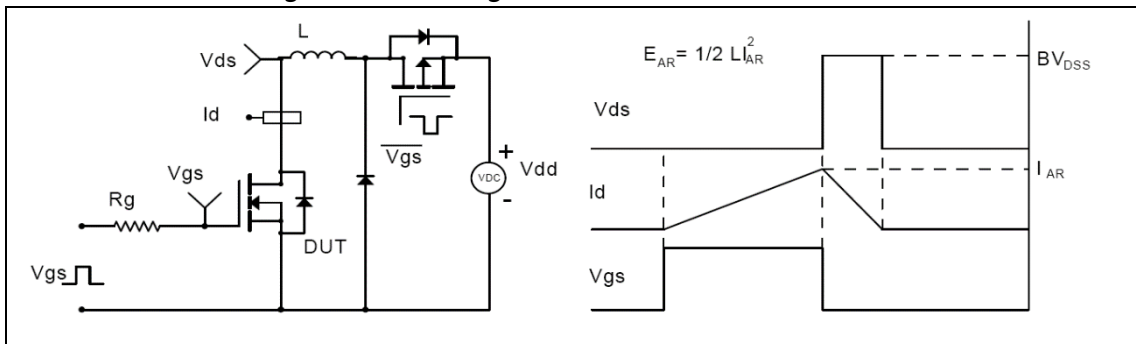


Figure 3, Unclamped inductive switching (UIS) test circuit & waveforms

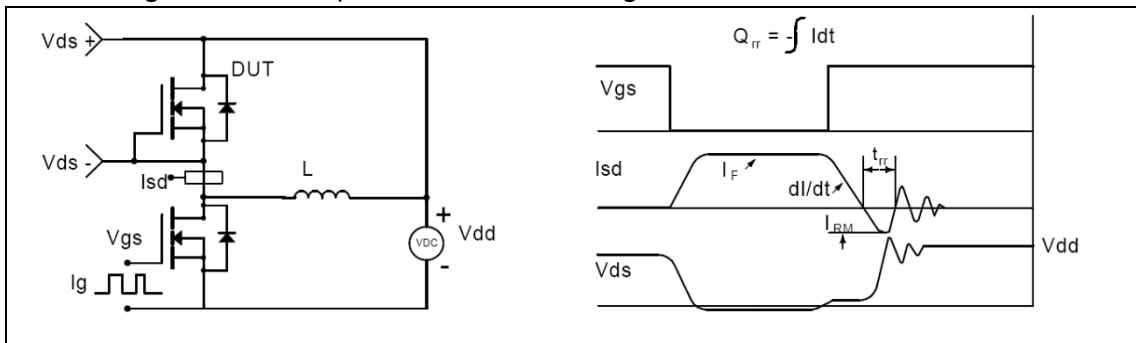
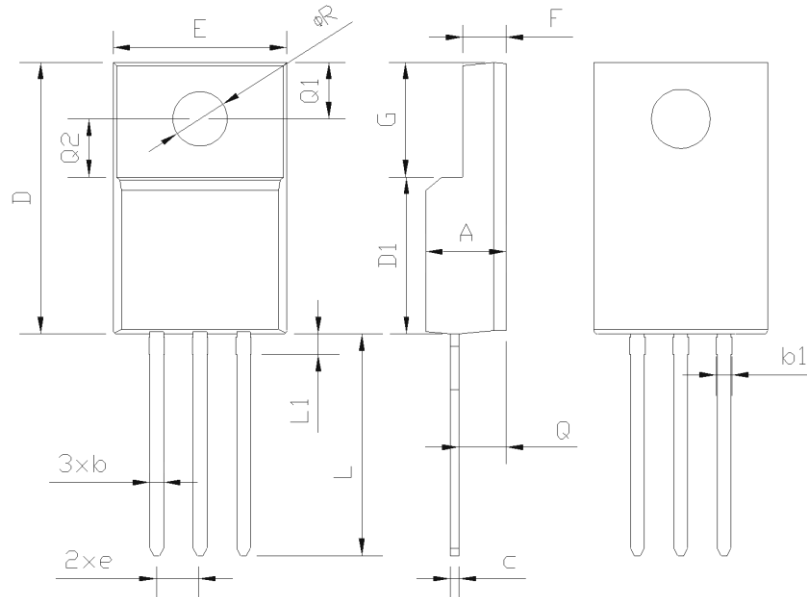


Figure 4, Diode reverse recovery test circuit & waveforms

**■ Package Information**

Figure1, TO220F\_NL package outline dimension



SYMBOL	mm		
	MIN	NOM	MAX
A	4.30	4.50	4.70
b	0.60	0.70	0.80
b1	0.60	0.80	0.90
c	0.45	0.50	0.60
D	14.70	15.00	15.30
D1	8.50 REF.		
e	2.60 BSC.		
E	9.70	10.00	10.30
F	2.50	2.70	2.90
G	6.30	6.50	6.70
L	13.40	13.60	13.80
L1	1.00	1.10	1.20
Q	2.50	2.60	2.70
Q1	2.90	3.00	3.10
Q2	3.50 REF.		
ΦR	3.00	3.20	3.40



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**■ Ordering Information**

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Package	Units/Tube	Tubes/Inner Box	Units/Inner Box	Inner Box/Carton Box	Units/Carton Box
TO220F	50	40	2000	4	8000

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**■ Product Information**

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Product	Package	Pb Free	RoHS	Halogen Free
OSG65R260FSF_NB	TO220F	yes	yes	yes

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